

Field effect rectifier

Datasheet - production data

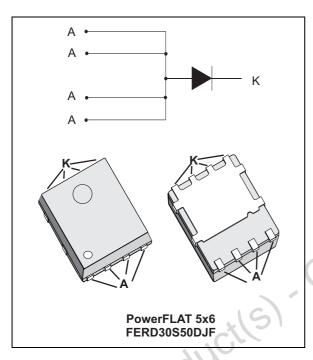


Table 1. Device summary

Symbol	Value
I _{F(AV)}	30 A
V_{RRM}	50 V
T _j (max)	+150 °C
V _F (typ)	0.33 V

Features

- CMOS proprietary process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

Description

This single rectifier is based on a proprietary technology, enabling to achieve the best in class $V_{\text{F}}/I_{\text{R}}$ trade-off for a given silicon surface.

Packaged in PowerFLAT™ 5x6, this device is intended to be used in rectification and freewheeling operations in switch-mode power supplies.

TM: PowerFLAT is a trademark of STMicroelectronics

Characteristics FERD30S50

1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, anode terminals short-circuited)

Symbol	Parameter			Unit
V_{RRM}	Repetitive peak reverse voltage			V
I _{F(RMS)}	Forward rms current			Α
I _{F(AV)}	Average forward current, δ = 0.5 T_c = 95 °C		30	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	180	Α
T _{stg}	Storage temperature range			°C
T _j ⁽¹⁾	Maximum operating junction temperature			°C

^{1.} $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

Symbo		Parameter	10/10	Value (max)	Unit
R _{th(j-c)}	Junction to case		60/	2.6	°C/W

Table 4. Static electrical characteristics (anode terminals short-circuited)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
		T _j = 125 °C	V _R = 35 V		25		
I _R ⁽¹⁾	I _R ⁽¹⁾ Reverse leakage current	T _j = 25 °C	M M			8.0	mA
15 00,0	T _j = 125 °C	$V_R = V_{RRM}$		30	60		
V _F ⁽²⁾ Forward voltage drop	T _j = 25 °C	I _F = 5 A		0.32			
	T _j = 125 °C	IF = 3 A		0.25			
	T _j = 25 °C	I _F = 10 A		0.37		V	
	T _j = 125 °C	I _F = 10 A		0.33		V	
O_2		T _j = 25 °C	I _F = 15 A		0.415	0.47	
	T _j = 125 °C	I _F = 13 A		0.39	0.45		

^{1.} Pulse test: $t_p = 5 \text{ ms}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.205 \times I_{F(AV)} + 0.017 I_{F^{2}(RMS)}^{2}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

FERD30S50 Characteristics

Figure 1. Average forward power dissipation versus average forward current

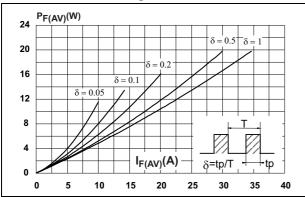


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$)

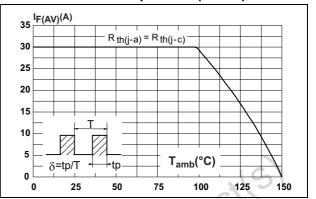
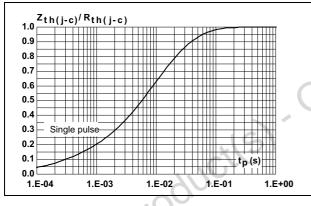


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values)



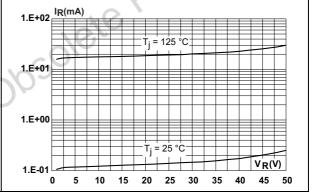
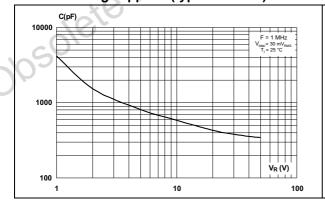
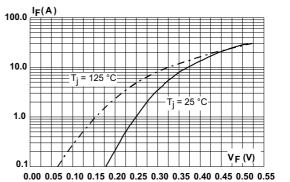


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

Figure 6. Forward voltage drop versus forward current (typical values)





Characteristics **FERD30S50**

 $R_{th(j-a)}(^{\circ}C/W)$ 150 Epoxy printed board Fr4, copper thickness = 35 μm 125 100 75 50 Obsolete Product(s) 25

Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)

S_{Cu}(cm²)

9

10

8

Package information 2

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

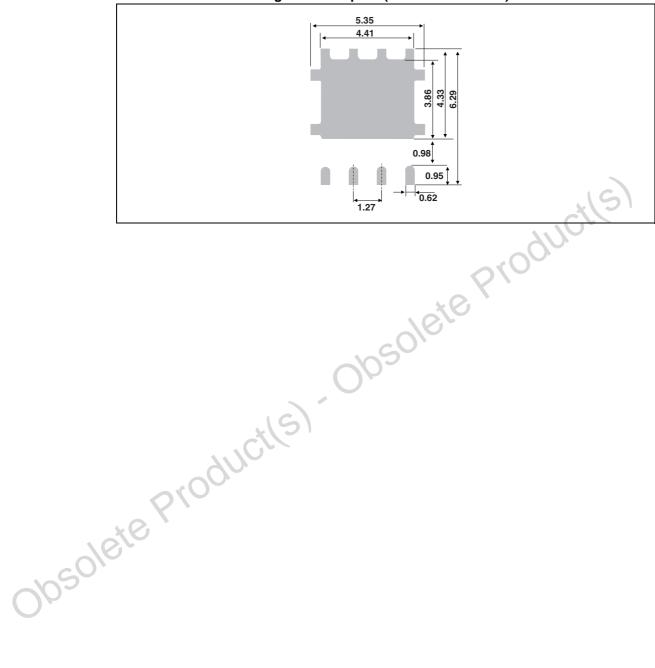
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 8. PowerFLAT-8L dimensions (definitions)

Table 5. PowerFLAT-8L dimensions (values)

	01	Dimensions					
	Ref.	Millimeters			Inches		
7/6		Min.	Тур.	Max.	Min.	Тур.	Max.
-501	Α	0.80		1.00	0.031		0.039
Ob	A1	0.02		0.05	0.001		0.002
	A2		0.25			0.010	
	b	0.30		0.50	0.012		0.020
	D		5.20			0.205	
	D2	4.11		4.31	0.162		0.170
	е		1.27			0.050	
	E		6.15			0.242	
	E2	3.50		3.70	0.138		0.146
	L	0.50		0.80	0.020		0.031
	К	1.275		1.575	0.050		0.062

Figure 9. Footprint (dimensions in mm)





3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD30S50DJF	FD30S50	PowerFLAT 5x6	95 mg	3000	Tape and reel

4 Revision history

Table 7. Document revision history

	Table 11 Decament revision motory					
	Date	Revision	Changes			
	28-Jun-2013	1	Initial release.			
	18-Nov-2013	2	Updated <i>Table 1</i> and <i>Table 4</i> . Inserted new <i>Figure 1</i> , <i>Figure 2</i> , <i>Figure 4</i> and <i>Figure 6</i> . Product name changed from FERD30S50DJF to FERD30S50.			
Obsole	te Prodi	sct(s)	305°01			

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

8/8

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries. Information in this document supersedes and replaces all information previously supplied. The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2013 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

Doc ID024715 Rev 2

